

## isc N-Channel Mosfet Transistor

**IRF820FI**

### • FEATURES

- Low  $R_{DS(on)} = 2.5 \Omega$  (TYP)
- Lower Input Capacitance
- Improved Gate Charge
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • DESCRIPTION

High current , high speed switching

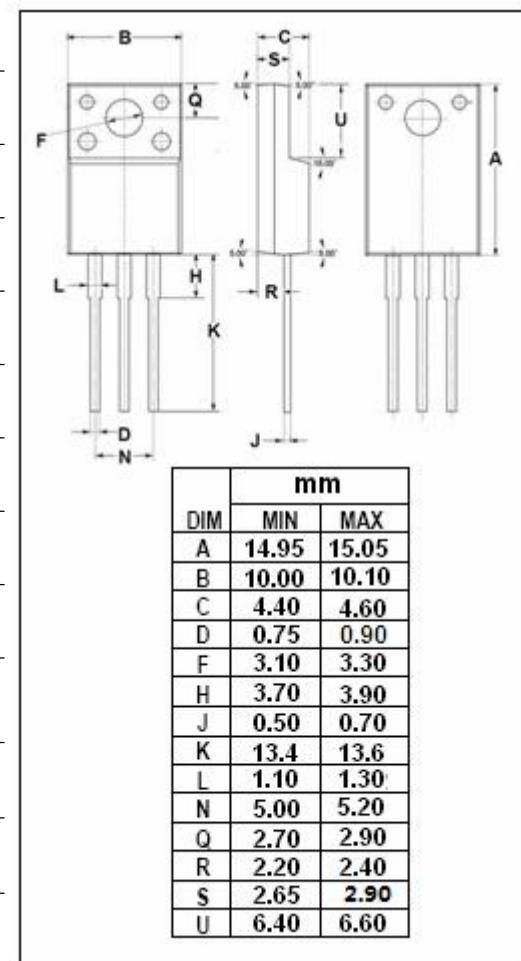
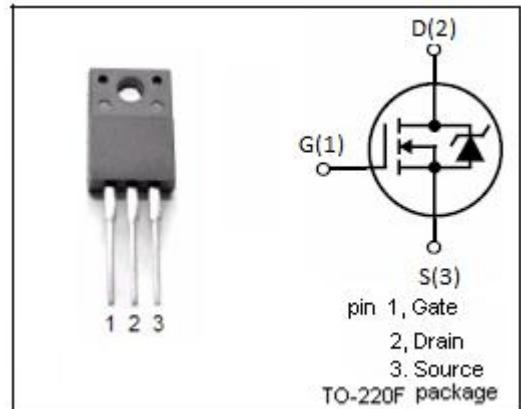
- Switching mode power supplies
- DC-DC & DC-AC converter

### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	500	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $TC=25^\circ\text{C}$	2.2	A
$I_{DM}$	Drain Current-Single Plused	12	A
$P_{tot}$	Total Dissipation@ $TC=25^\circ\text{C}$	35	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	3.57	$^\circ\text{C/W}$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	62.5	$^\circ\text{C/W}$



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## ELECTRICAL CHARACTERISTICS

 $T_c=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}= 0; I_D=0.25\text{mA}$	500			V
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}= V_{\text{GS}}; I_D=0.25\text{mA}$	2.0		4.0	V
$V_{\text{SD}}$	Diode Forward On-voltage	$I_S= 3\text{A}; V_{\text{GS}}= 0$			1.6	V
$R_{\text{DS}(\text{on})}$	Drain-Source On-Resistance	$V_{\text{GS}}= 10\text{V}; I_D= 1.5\text{A}$		2.5	3.0	$\Omega$
$I_{\text{GSS}}$	Gate-Body Leakage Current	$V_{\text{GS}}= \pm 20\text{V}; V_{\text{DS}}= 0$			$\pm 100$	nA
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}=500\text{V}; V_{\text{GS}}= 0$			250	$\mu\text{A}$
$G_{\text{fs}}$	Forward Transconductance	$V_{\text{DS}}= 25\text{V}; I_D=1.5\text{A}$	0.8			S
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$I_D=1.5\text{A}; V_{\text{DD}}=250\text{V}; R_G=50\ \Omega$			45	ns
$t_r$	Rise Time				110	
$t_{\text{d}(\text{off})}$	Turn-off Delay Time				215	
$t_f$	Fall Time				80	

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